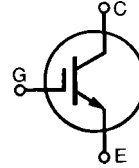


## HiPerFAST™ IGBT

IXGA 7N60B

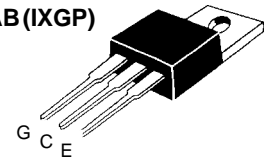
IXGP 7N60B

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 14 \text{ A} \\ V_{CE(sat)} &= 2 \text{ V} \\ t_{fi} &= 150 \text{ ns} \end{aligned}$$

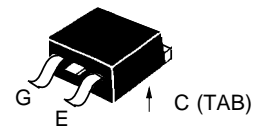


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	14	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	7	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	30	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 300 \mu\text{H}$	$I_{CM} = 14$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	54	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque, (TO-220)	M3 0.45/4 M3.5 0.55/5	Nm/lb.in.
<b>Weight</b>	TO-220	4	g
	TO-263	2	g

TO-220AB (IXGP)



TO-263 AA (IXGA)



G = Gate,      C = Collector,  
E = Emitter,    TAB = Collector

**Features**

- International standard packages JEDEC TO-263 surface mountable and JEDEC TO-220 AB
- Medium frequency IGBT
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on - drive simplicity

**Applications**

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

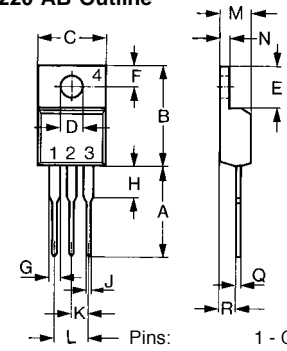
**Advantages**

- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
$I_{CES}$	$V_{CE} = 0.8 V_{CES}, T_J = 25^\circ\text{C}$ $V_{GE} = 0 \text{ V}, T_J = 125^\circ\text{C}$			100 $\mu\text{A}$ 500 $\mu\text{A}$
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	1.8	2.0	V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}, V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	3	7	S
$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		500	pF
$C_{oes}$			50	pF
$C_{res}$			17	pF
$Q_g$	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		25	nC
$Q_{ge}$			5	nC
$Q_{gc}$			10	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 300\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 22\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 V_{CES}$ , higher $T_J$ or increased $R_G$		9	ns
$t_{ri}$			10	ns
$E_{on}$			0.07	mJ
$t_{d(off)}$			100	200 ns
$t_{fi}$			150	250 ns
$E_{off}$			0.3	0.6 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 300\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 22\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 V_{CES}$ , higher $T_J$ or increased $R_G$		10	ns
$t_{ri}$			15	ns
$E_{on}$			0.15	mJ
$t_{d(off)}$			200	ns
$t_{fi}$			250	ns
$E_{off}$			0.6	mJ
$R_{thJC}$				2.3 K/W
$R_{thCK}$	(TO-220)		0.25	K/W

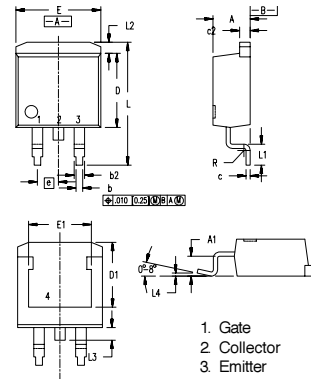
### TO-220 AB Outline



Pins:  
1 - Gate  
2 - Collector  
3 - Emitter  
4 - Collector  
Bottom Side

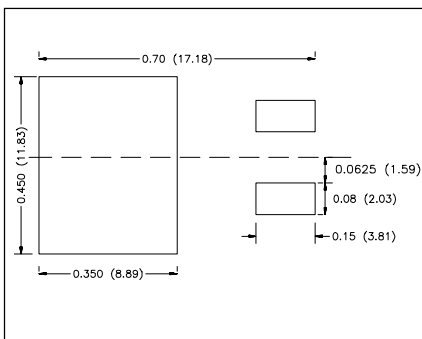
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

### TO-263 AA Outline



1. Gate  
2. Collector  
3. Emitter  
4. Collector  
Bottom Side

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029



### Min. Recommended Footprint (Dimensions in inches and mm)

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592    4,881,106    5,017,508  
4,850,072    4,931,844    5,034,796

5,049,961    5,187,117  
5,063,307    5,237,481

5,486,715    6,308,728B1  
5,381,123